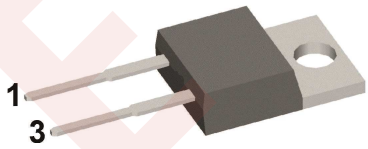
Sonic Fast Recovery Diode

V_{RRM}	=	1800 V
I_{FAV}	=	10 A
t_{rr}	=	260 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

Part number

DHG10I1800PA



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Fast Diode				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
I_R	*reverse current, drain current*	V_R = 1800 V	T_{VJ} = 25°C			50	µA
		V_R = 1800 V	T_{VJ} = 150°C			0.4	mA
V_F	*forward voltage drop*	I_F = 10 A	T_{VJ} = 25°C			2.27	V
		I_F = 20 A				2.94	V
		I_F = 10 A	T_{VJ} = 150°C			2.43	V
		I_F = 20 A				3.42	V
I_{FAV}	*average forward current*	T_C = 110°C rectangular d = 0.5	T_{VJ} = 175°C			10	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			1.40	V
r_F	*slope resistance*					101	mΩ
R_{thJC}	*thermal resistance junction to case*					1.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.5		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			85	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			60	A
C_J	*junction capacitance*	V_R = 900 V f = 1 MHz	T_{VJ} = 25°C		3		pF
I_{RM}	*max. reverse recovery current*	I_F = 10 A; V_R = 900 V $-di_F/dt$ = 350 A/µs	T_{VJ} = 25 °C		15		A
			T_{VJ} = 150 °C		17.5		A
t_{rr}	*reverse recovery time*		T_{VJ} = 25 °C		260		ns
			T_{VJ} = 150 °C		350		ns

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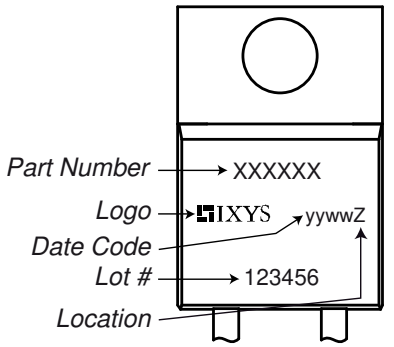
Package TO-220			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			35	A
T_{VJ}	*virtual junction temperature*		-55		175	°C
T_{op}	*operation temperature*		-55		150	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N

Product Marking



Part description

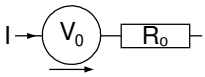
D = Diode
H = Sonic Fast Recovery Diode
G = extreme fast
10 = Current Rating [A]
I = Single Diode
1800 = Reverse Voltage [V]
PA = TO-220AC (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10I1800PA	DHG10I1800PA	Tube	50	508242

Similar Part	Package	Voltage class
DHG10IM1800UZ	TO-252AA (DPak) (2HV)	1800

Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 175°C$



		Fast Diode	
$V_{0\,max}$	*threshold voltage*	1.4	V
$R_{0\,max}$	*slope resistance **	98	mΩ

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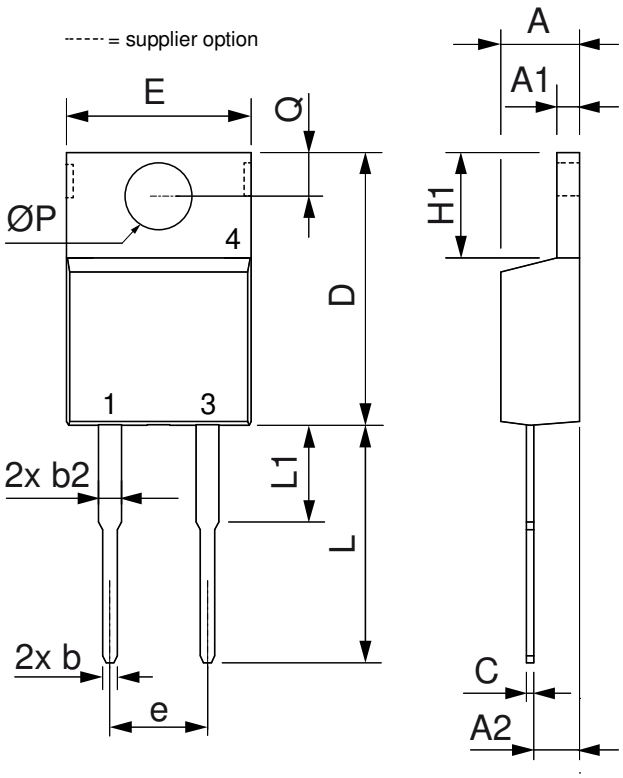
Outlines TO-220



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125

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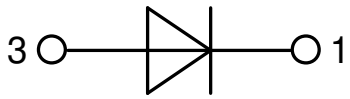

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Fast Diode

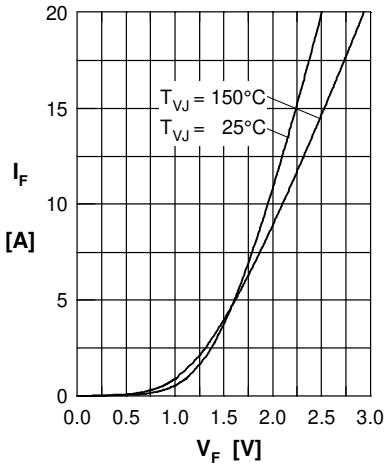

Fig. 1 Typ. Forward current versus V_F

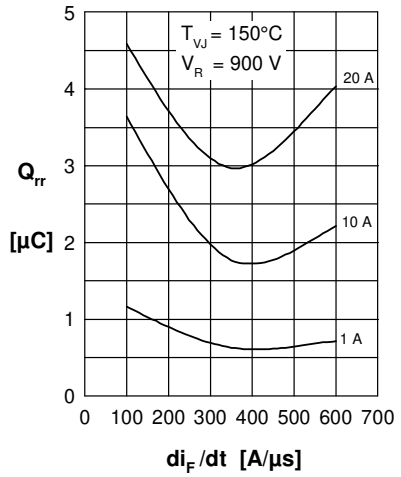

Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

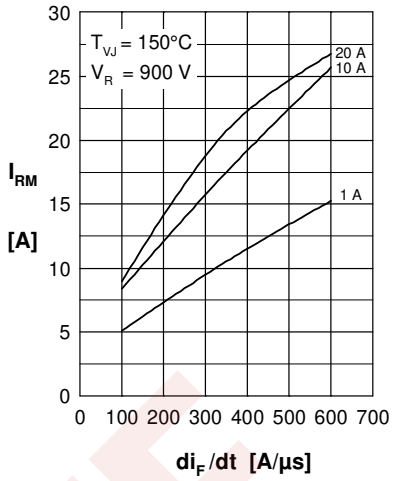

Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

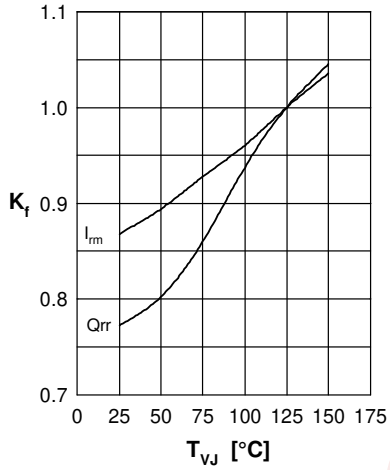

Fig. 4 Dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

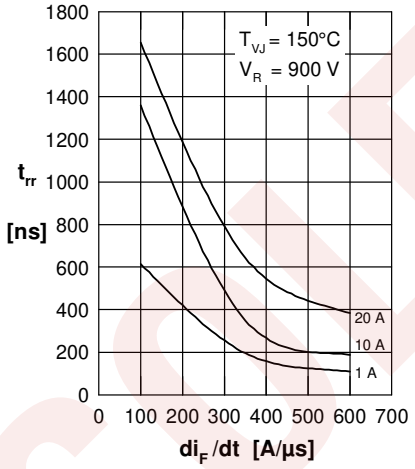

Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

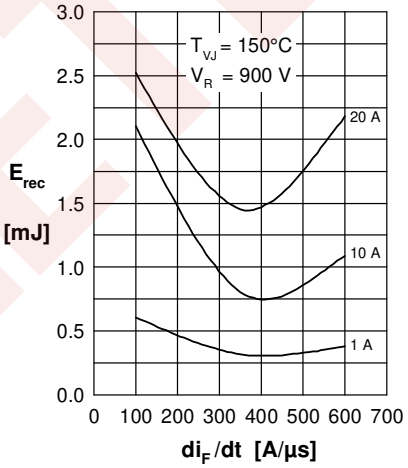

Fig. 6 Typ. recovery energy E_{rec} versus di/dt

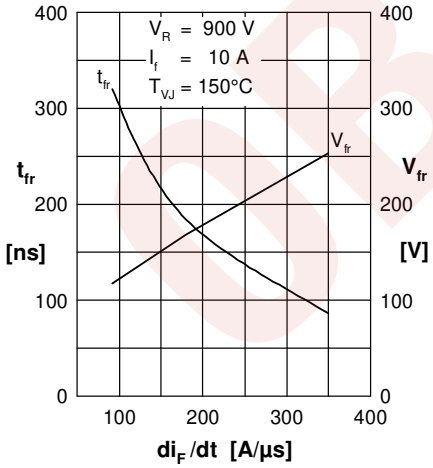

Fig. 7 Typ. peak forward voltage Vfr_{fr} and t_{fr} versus di_F/dt

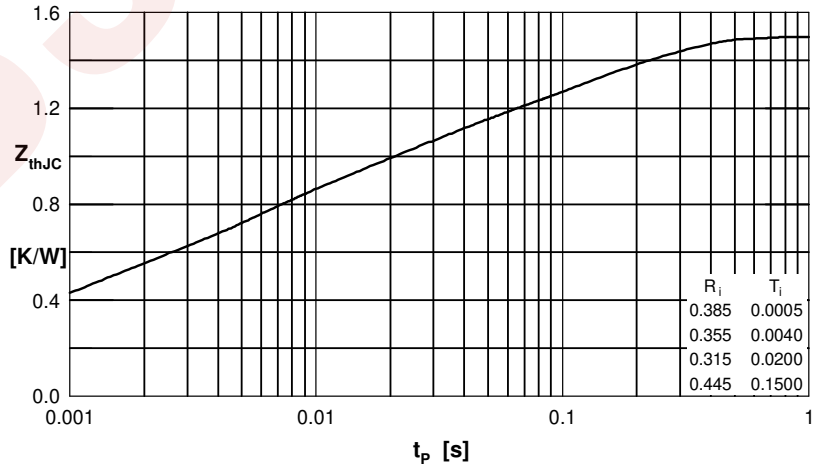

Fig. 8 Typ. transient thermal impedance junction to case

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